

7/10/03

Sheet 1 of 1

FORM PTO-1449 (Modified)	U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE	ATTY. DOCKET NO. 06293P2 USA	SERIAL NO. 10/616,662
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use several sheets if necessary)		APPLICANT Peng Zhang, et al.	
		FILING DATE	GROUP

(37 CFR 1.98(b))

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U.S. PATENT DOCUMENTS

EXAM- INER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE (IF APPROPRIATE)
<i>W</i>	0 0 5 5 6 6 0	5/9/2002	K. R. Lassila, et al.	568	616	10/11/2001
<i>W</i>	5 9 4 8 4 6 4	9/7/1999	F. M. Delnick	427	77	6/19/1996
<i>W</i>	5 9 7 7 0 4 1	11/2/1999	K. Honda	510	175	9/23/1997
<i>W</i>	6 1 5 2 1 4 8	11/28/2000	A. M. George, et al.	134	2	9/3/1998
<i>W</i>	6 3 1 3 1 8 2	11/6/2001	K. R. Lassila, et al.	516	204	5/4/1999
<i>W</i>	0 1 1 5 0 2 2	8/22/2002	S. A. Messick, et al.	430	311	2/21/2001

FOREIGN PATENT DOCUMENTS

	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION
						YES NO
<i>W</i>	EP 1 1 1 5 0 3 5	7/2001	Europe			X
<i>W</i>	JP 95 1 4 2 3 4 9	6/1995	Japan			X
<i>W</i>	JP 96 0 0 8 1 6 3	1/1996	Japan			X
<i>W</i>	WO 0 0 0 3 3 0 6	1/2000	World			X
<i>W</i>	WO 0 2 2 3 5 9 8	3/2002	World			X
<i>W</i>	WO 8 7 0 3 3 8 7	6/1987	World			X
<i>W</i>	WO 9 9 1 5 6 0 9	4/1999	World			X
<i>W</i>	WO 9 9 6 0 0 8 3	1/1999	World			X
<i>W</i>	WO 9 9 6 0 4 4 8	1/1999	World			X

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OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

<i>W</i>	Domke, W. D., et al., "Pattern Collapse in High Aspect Ratio DUV and 193nm Resists," Proc. SPIE-Int. Soc. Opt. Eng. 3999, 313-321, 2000.
<i>W</i>	Cheung, C., et al., "A Study of a Single Closed Contact for 0.18 Micron Photolithography Process," Proc. SPIE-Int. Soc. Opt. Eng. 3998, 738-741, 2000.
<i>W</i>	S. Hien, et al., "Collapse behavior of single layer 193 and 157 nm resists: Use of surfactants in the rinse to realize the sub 130 nm nodes," Infineon Technologies, International SEMATECH, Center for Nano Technology, University of Wisconsin.
<i>W</i>	T. Tanaka, et al., "Mechanism of Resist Pattern Collapse During Development Process," Jpn. J. Appl. Phys. Vol. 32 (1993), pp. 6059-6064, Part 1, No. 12B.

EXAMINER <i>[Signature]</i>	DATE CONSIDERED 9/5/2005
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EXAMINER: Initial citation considered. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.